carrying out a second heat treatment to getter the catalytic element into the source region and the drain region; and

carrying out a third heat treatment for the crystalline semiconductor thin film at 900 to 1200°C in a reducing atmosphere.

22. A method of fabricating a crystalline semiconductor thin film, comprising the steps of:

adding a catalytic element for facilitating crystallization of an amorphous semiconductor thin film to the amorphous semiconductor thin film;

carrying out a first heat treatment to transform the amorphous semiconductor thin film into a crystalline semiconductor thin film by irradiating ultraviolet light or infrared light; and

carrying out a second heat treatment for the crystalline semiconductor thin film at 900 to 1200°C in an atmosphere containing hydrogen therein.

23. A method of fabricating a crystalline semiconductor thin film, comprising the steps of:

adding a catalytic element for facilitating crystallization of an amorphous semiconductor thin film to the amorphous semiconductor thin film;

carrying out a first heat treatment to transform the amorphous semiconductor thin film into a crystalline semiconductor thin film by irradiating ultraviolet light or infrared light; and

carrying out a second heat treatment for the crystalline semiconductor thin film at 900 to 1200°C in an atmosphere containing ammonia therein.--

## REMARKS

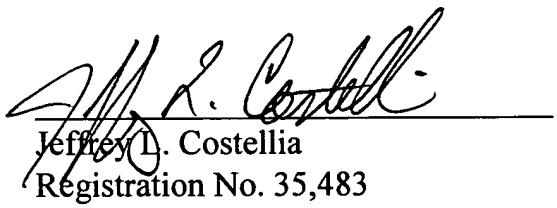
The Official Action mailed July 10, 2000 has been received and its contents carefully studied. Claims 1-18 were pending in the Official Action.

Applicants hereby elect Group II claims - that is, claims 5-18, drawn to a method of forming a structure classified in class 438, subclass 149,479 and 517. Further, Applicants add claims 19-23 herewith, which are also believed to be readable on the elected embodiment. Thus, claims 5-23 are pending and are believed to be subject to examination.

In addition, Applicants amend the specification on page 30 to change the reference to the group of the Periodic Table of Elements from group "15" to group --VA--. As clearly provided by the attached Periodic Table of Elements group "15" is a "new notation" that corresponds to the CAS version group "VA". Therefore, no new matter is introduced by this amendment, but instead merely amends the specification to comply with standard U.S. chemical practice.

Favorable consideration is requested.

Respectfully submitted,



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# Periodic table of the elements

| 1 Group IA | 2 | New notation → | | | | | | | | | | 13 IIIB IIIA | 14 IVB IVA | 15 VB VA | 16 VIB VIA | 17 VIIB VIIA | 18 VIIIA |
|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|
| | | Previous IUPAC form → | | | | | | | | | | | | | | | |
| | | CAS version → | | | | | | | | | | | | | | | |
| 1 H 1.0079 | 2 IIA | | | | | | | | | | | | | | | | 2 He 4.00260 |
| 3 Li 6.941 | 4 Be 9.01218 | | | | | | | | | | | 5 B 10.81 | 6 C 12.011 | 7 N 14.0067 | 8 O 15.9994 | 9 F 18.9984 | 10 Ne 20.179 |
| 11 Na 22.9898 | 12 Mg 24.305 | 3 IIIA IIIB | 4 IVA IVB | 5 VA VB | 6 VIA VIB | 7 VIIA VIIB | 8 | 9 VIIIA VIII | 10 | 11 IB | 12 IIB | 13 Al 26.9815 | 14 Si 28.0855 | 15 P 30.9738 | 16 S 32.06 | 17 Cl 35.453 | 18 Ar 39.948 |
| 19 K 39.0983 | 20 Ca 40.08 | 21 Sc 44.9559 | 22 Ti 47.88 | 23 V 50.9415 | 24 Cr 51.996 | 25 Mn 54.9380 | 26 Fe 55.847 | 27 Co 58.9332 | 28 Ni 58.69 | 29 Cu 63.546 | 30 Zn 65.39 | 31 Ga 69.72 | 32 Ge 72.59 | 33 As 74.9216 | 34 Se 78.96 | 35 Br 79.904 | 36 Kr 83.80 |
| 37 Rb 85.4678 | 38 Sr 87.62 | 39 Y 88.9059 | 40 Zr 91.224 | 41 Nb 92.9064 | 42 Mo 95.94 | 43 Tc (98) | 44 Ru 101.07 | 45 Rh 102.906 | 46 Pd 106.42 | 47 Ag 107.868 | 48 Cd 112.41 | 49 In 114.82 | 50 Sn 118.71 | 51 Sb 121.75 | 52 Te 127.60 | 53 I 126.905 | 54 Xe 131.29 |
| 55 Cs 132.905 | 56 Ba 137.33 | 57 La ★ 138.906 | 72 Hf 178.49 | 73 Ta 180.948 | 74 W 183.85 | 75 Re 186.207 | 76 Os 190.2 | 77 Ir 192.22 | 78 Pt 195.08 | 79 Au 196.967 | 80 Hg 200.59 | 81 Tl 204.383 | 82 Pb 207.2 | 83 Bi 208.980 | 84 Po (209) | 85 At (210) | 86 Rn (222) |
| 87 Fr (223) | 88 Ra 226.025 | 89 Ac ▲ 227.028 | 104 [a] Unq (261) | 105 [a] Unp (262) | 106 [a] Unh (263) | 107 [a] Uns (262) | | | | | | | | | | | |

| ★ Lanthanide series | 58 Ce 140.12 | 59 Pr 140.908 | 60 Nd 144.24 | 61 Pm (145) | 62 Sm 150.36 | 63 Eu 151.96 | 64 Gd 157.25 | 65 Tb 158.925 | 66 Dy 162.50 | 67 Ho 164.930 | 68 Er 167.26 | 69 Tm 168.934 | 70 Yb 173.04 | 71 Lu 174.96 |
|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|
| ▲ Actinide series | 90 Th 232.038 | 91 Pa 231.036 | 92 U 238.029 | 93 Np 237.048 | 94 Pu (244) | 95 Am (243) | 96 Cm (247) | 97 Bk (247) | 98 Cf (251) | 99 Es (252) | 100 Fm (257) | 101 Md (258) | 102 No (259) | 103 Lr (260) |

**Note:** Atomic masses shown here are the 1983 IUPAC values (maximum of six significant figures). [a] Symbols based on IUPAC systematic names.

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AUG 21 2000 TC 2800 MAIL ROOM

| Element |
|---|
| Actinium |
| Aluminum |
| Americium |
| Antimony |
| Argon |
| Arsenic |
| Astatine |
| Barium |
| Berkelium |
| Beryllium |
| Bismuth |
| Boron |
| Bromine |
| Cadmium |
| Calcium |
| Californium |
| Carbon |
| Cerium |
| Cesium |
| Chlorine |
| Chromium |
| Cobalt |
| Copper |
| Curium |
| Dysprosium |
| Einsteinium |
| Erbium |
| Europium |
| Fermium |
| Fluorine |
| Francium |
| Gadolinium |
| Gallium |
| Germanium |
| Gold |
| Hafnium |
| Helium |
| Holmium |
| Hydrogen |
| Indium |
| Iodine |
| Iridium |
| Iron |
| Krypton |
| Lanthanum |
| Lawrencium |
| Lead |
| Lithium |
| Lutetium |
| Magnesium |
| Manganese |
| Mendelevium |